

(19)
(12)

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(A)

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(43)

10-2004-0053495
2004 06 24

(21)

10-2002-0080054

(22)

2002 12 14

(71)

575

(72)

5

507 604

109 202

870

405 902

(74)

:

(54)

,

1 , , 1 2 가 1 4 ,

3 , 5 .

8

,

1 7 ,

8 ,

9

10

가 , TFT-LCD 가 가
가

2000 - 123971

가 가 , 가 가 가

9-7763

(U.S 6,426,274)

(method for making thin film semiconductor)

가 가
(epitaxial semiconductor film)

, U.S 6,326,280 , U.S 6,107,213 , U.S 5,811,348 , U.S 6,194,245 , U.S 6,194,239

가

가

1

1

가

가

1

1

2

1

3

4

5

4

4

2

3

가

1

1

2

1

3

4

가

5

가

2 ,

2 ,

1

1 , 1 ,

1 , 2 1 , 1 2 , 2

2 1 , 1

2

가

가

1 ,

2

1 7

1 (12) Si, , 100 1000 1 (12) (11)

2a 2c 1 (12) (20)

(20)

2a (21) 1 p n (21) 2b (23)

(23) (22) (24)

1 (25) 1 (25) (23) (22)

1 (25) (26) (27) (24)

1 (25) 2 (28a) 1 (25) 1 (28b)

(28) 2 (25a) 2c (26) 1 (25) 2 (25a)

(25a) 1 (29) 3 (30) 1 (29) 2

(31) , (31) 3 (30) 1 (29) 2 (32)

(20) 가

(20)

1 (11) (20) 3

(20) 2 (13) 4 (13 ;Passivea

2 (13) (14) (15)

(15) (thin glass) .

20 500 μ m .

(15) , 5 (11)

(15) (15) 3 (16)

(11) (15)

가 ,

(11) , 6 (11) 1 (20)

가 (17) , 1 (12)

(18) (1)

8) , (18) (11) 가 (11)

(19) 7 (11')

가 가 .

8

(51) , (50) 가 (51) , (60) ,

(60) 2 (52) , 2 (52) (60) ,

(67) 1 (53)

(51) 가 500 μ m 가 ,

(51) 20 500 μ m ,

(51) 1 (53) 9

(68)

(60) 2 (52) 2 (61) , (62) 1 (64)

(63) 1 (64) (66) (62) 1 (64)

(65) , (61) (51) , 1 (60) (64)

(65) 2 (61) 가 .

(60) 1 (53) 50 5000 ,

1 (53) 10 (55) 가 (55)

(55) 20 400 μ m 20 500 μ m

2 (61) 가 , 1 (64) (exiton) 1 (64) 가

(63) () 가 1 (61)

(51)

가 , 가

가

가

가 가 , 가

(57)

1. 가 ,

1 ,

1 ,

2.

1 ,

가

3.

가 1 ,

1 2 ,

1 3 ,

4 ,

5 .

4.

3 ,

4 , 2

5.

3 4 , 3 1 1 , 1 , 2

6.

3 , 4 , 3

7.

3 ,

8.

7 , 1

9.

3 , 5 1 1

10.

가 1 , 1 2 , 1 3 , 4 , 가 5

11.

10 , 가

12.

10 ,
4 , 2

13.
10 11 ,
3 1 1
1
2

14.
10 ,
4 , 3

15.
10 ,
1

16.
10 ,
5 1 1

17.
가 ,
2 ,
2 ,
1

18.
17 ,
1 ,

19.
17 ,
1

20.
19 ,

21.
17 ,

2 2 1 , 1 2 , 2
2

22.
21 ,

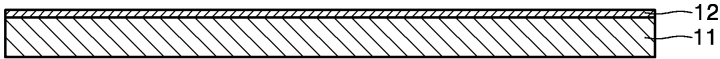
2

23.
19 ,

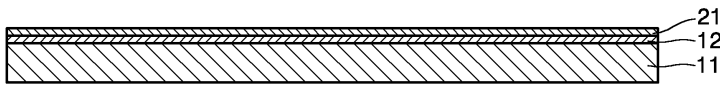
24.
17 ,

1

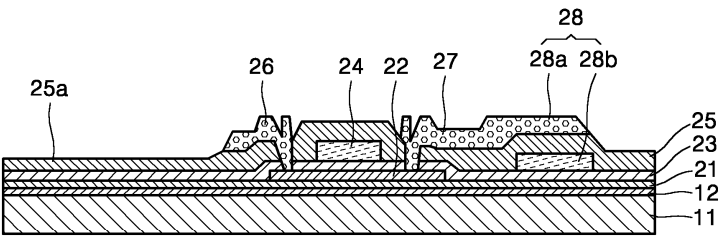
1



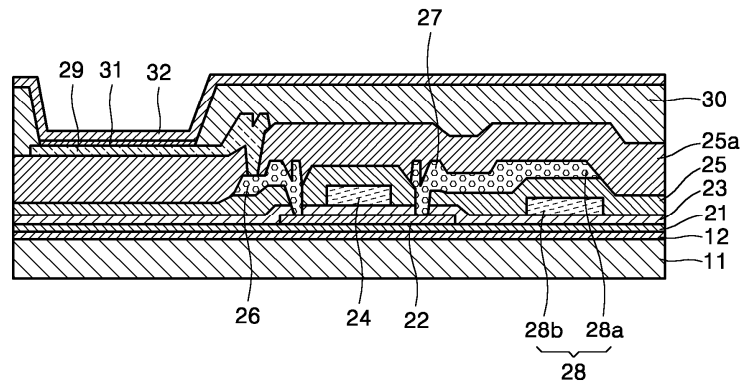
2a



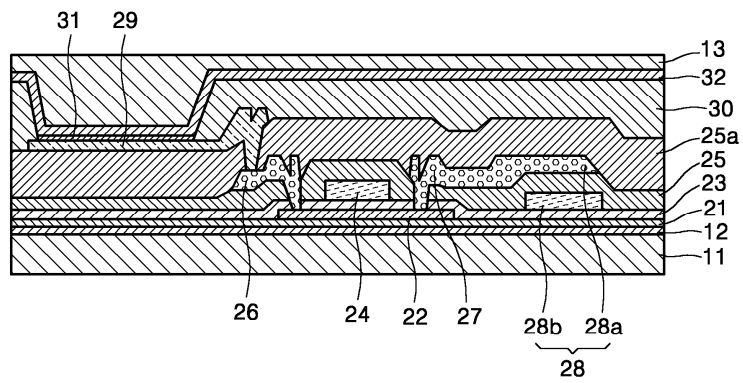
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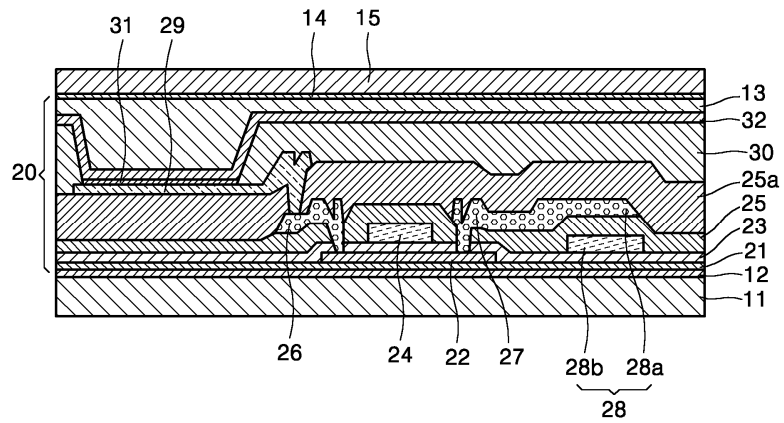
2c



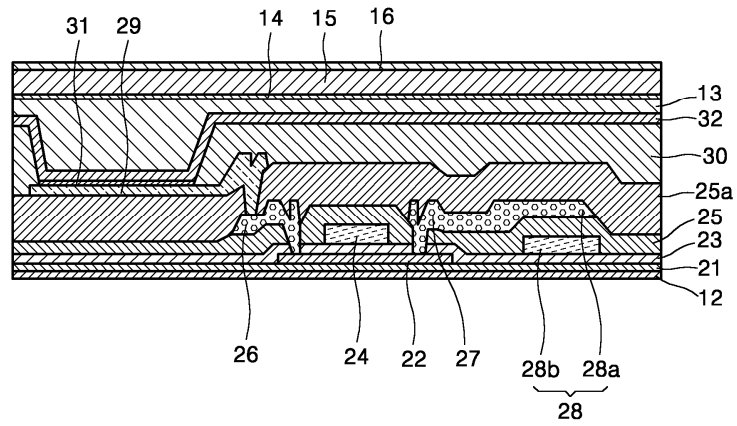
3



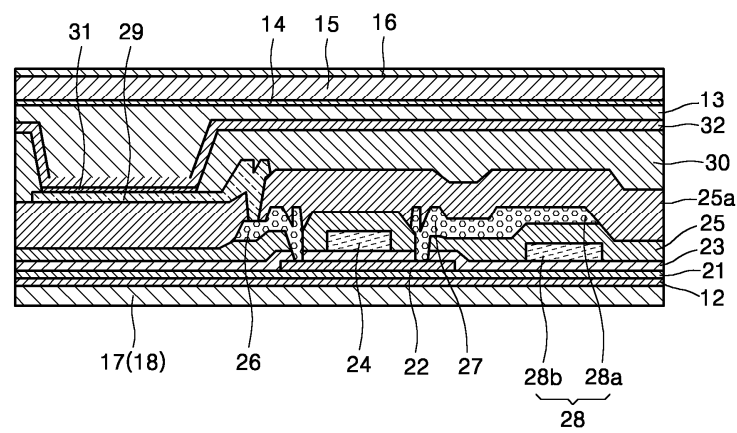
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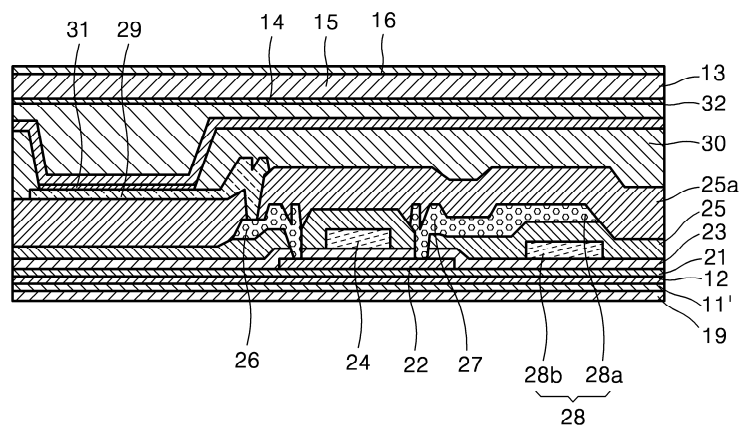
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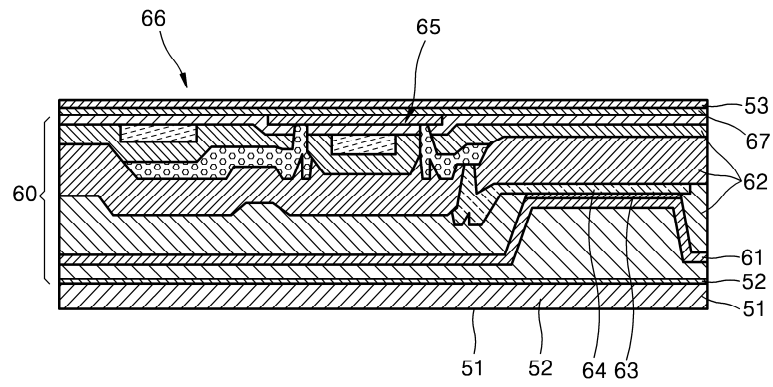
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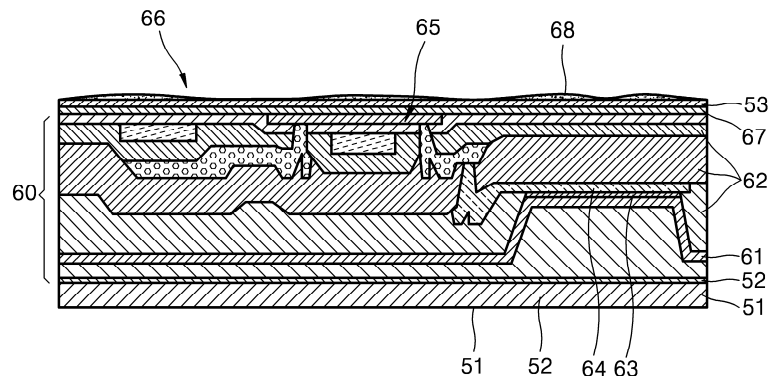
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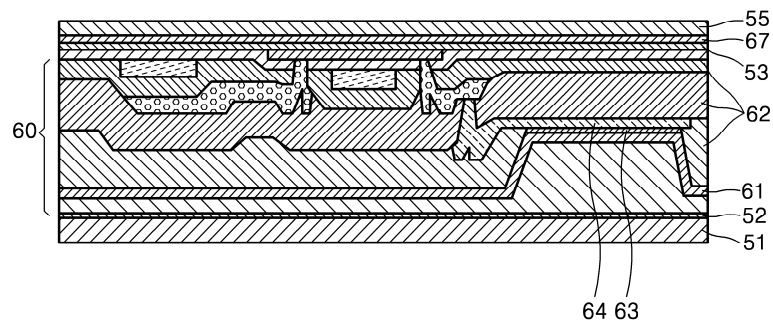
8



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专利名称(译)	基板制造方法，使用该基板制造方法的有机电致发光显示装置的制造方法，以及有机电致发光显示器		
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申请(专利权)人(译)	三星SD眼有限公司		
当前申请(专利权)人(译)	三星SD眼有限公司		
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发明人	박진우 정호균 송승용		
IPC分类号	H01L27/32 H05B33/10 H01L27/12 H01L51/56 H01L21/84 H01L21/77		
CPC分类号	H01L27/3244 H01L51/56 H01L2251/5338 H01L2227/326 H01L27/1214 H01L27/1266 H01L27/12 H01L51/524 Y10S438/977 H01L51/5253 H01L27/1218		
代理人(译)	LEE, YOUNG PIL 李，杨HAE		
其他公开文献	KR100484109B1		
外部链接	Espacenet		

摘要(译)

根据本发明，有机电致发光显示装置的制造方法包括第五步骤蚀刻，第二步骤在第一步骤的上侧形成第一保护膜，制备和子板，第三步骤在上部形成有机发光部分第一保护膜的一侧，第四步骤，柔性主板连接到有机发光部分的上侧，子板，并去除具有刻面平面的不具有柔性的子板。有机层和柔性基板。

